

1. General description

Planar passivated high commutation three quadrant triac in a SOT223 surface mountable plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct gate triggering from low power drivers and logic ICs
- High commutation capability with very sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

3. Applications

- Low power motor controls
- Small inductive loads e.g. solenoids, door locks, water valves
- Small loads in large white goods

4. Quick reference data

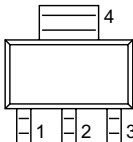
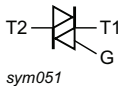
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Absolute maximum rating						
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{sp}} \leq 111\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_{\text{p}} = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	9	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_{\text{p}} = 16.7\text{ ms}$	-	-	9.9	A
T_{j}	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G+; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	0.25	-	5	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G-; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	0.25	-	5	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2- G-; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	0.25	-	5	mA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I _H	holding current	V _D = 12 V; T _J = 25 °C; Fig. 11		-	-	10	mA
V _T	on-state voltage	I _T = 0.85 A; T _J = 25 °C; Fig. 12		-	1.35	1.6	V
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _J = 125 °C; R _{GK} = 220 Ω; (V _{DM} = 67% of V _{DRM}); exponential waveform		200	-	-	V/μs
dI _{comf} /dt	rate of change of commutating current	V _D = 400 V; T _J = 125 °C; I _{T(RMS)} = 0.8 A; dV _{comf} /dt = 10 V/μs; gate open circuit		0.5	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
4	T2	main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA2008W-800D	SOT223	BTA2008W-800D,135	Reel	4000	SOT223	16-Mar-2006

7. Marking

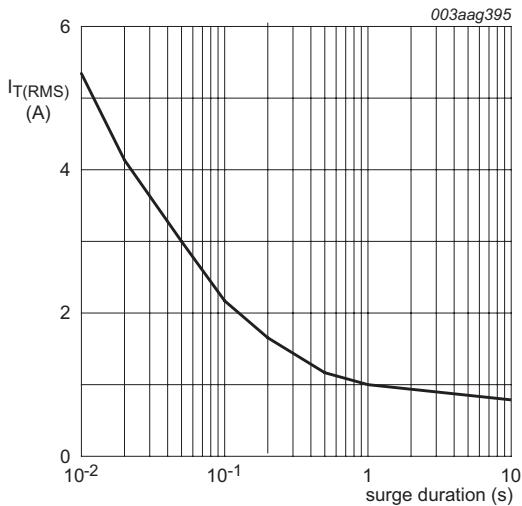
Table 4. Marking codes

Type number	Marking codes	
	Assembly factory: d	Assembly factory: L
BTA2008W-800D	Jdxxx 8D 2008W	JLxxx 8D 2008W

8. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{sp}} \leq 111\text{ }^{\circ}\text{C}$; Fig 1 ; Fig 2 ; Fig 3		-	0.8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; Fig 4 ; Fig 5		-	9	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 16.7\text{ ms}$		-	9.9	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; SIN		-	0.41	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{G}} = 20\text{ mA}$		-	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current			-	2	A
P_{GM}	peak gate power			-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period		-	0.1	W
T_{stg}	storage temperature			-40	150	$^{\circ}\text{C}$
T_{j}	junction temperature			-	125	$^{\circ}\text{C}$



$f = 50\text{ Hz}$; $T_{\text{sp}} = 111\text{ }^{\circ}\text{C}$
Fig. 1. RMS on-state current as a function of surge duration; maximum values

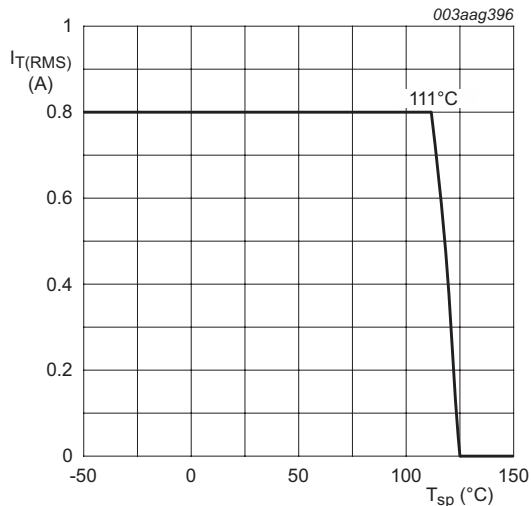


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

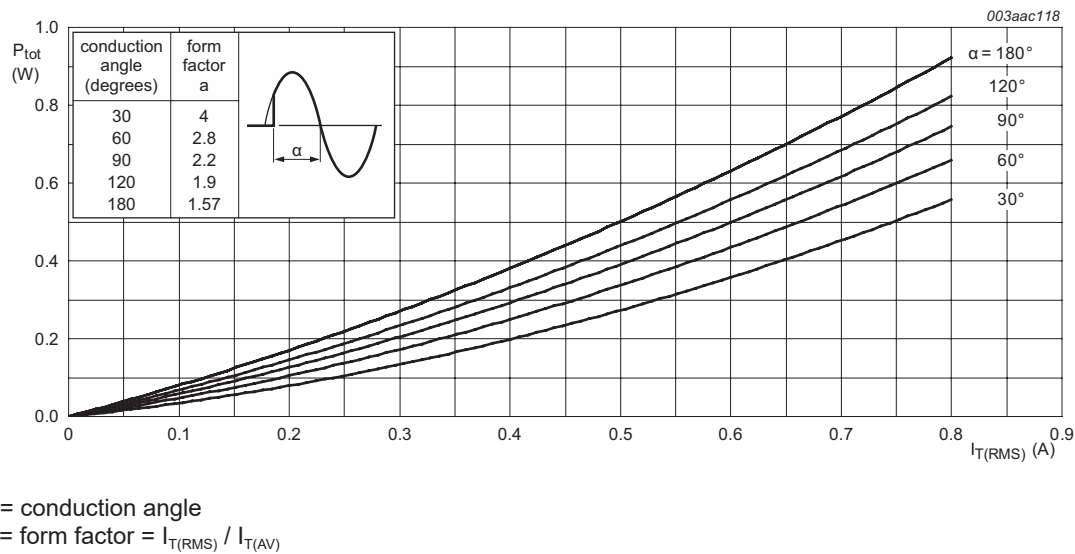


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

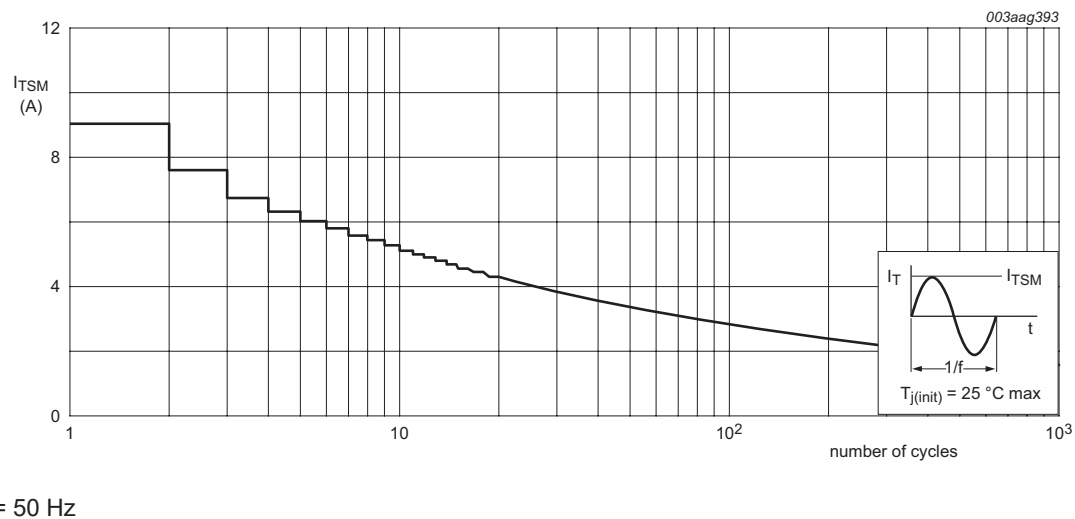


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

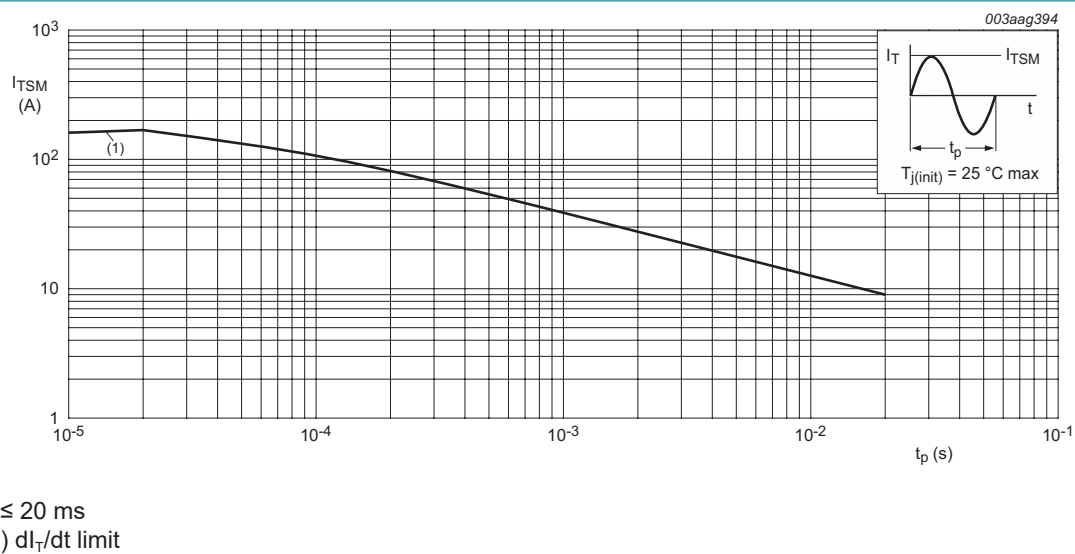


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle; Fig 6		-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; printed-circuit board mounted; minimum footprint; Fig 7		-	156	-	K/W
		in free air; printed-circuit board mounted; pad area; Fig 8		-	70	-	K/W

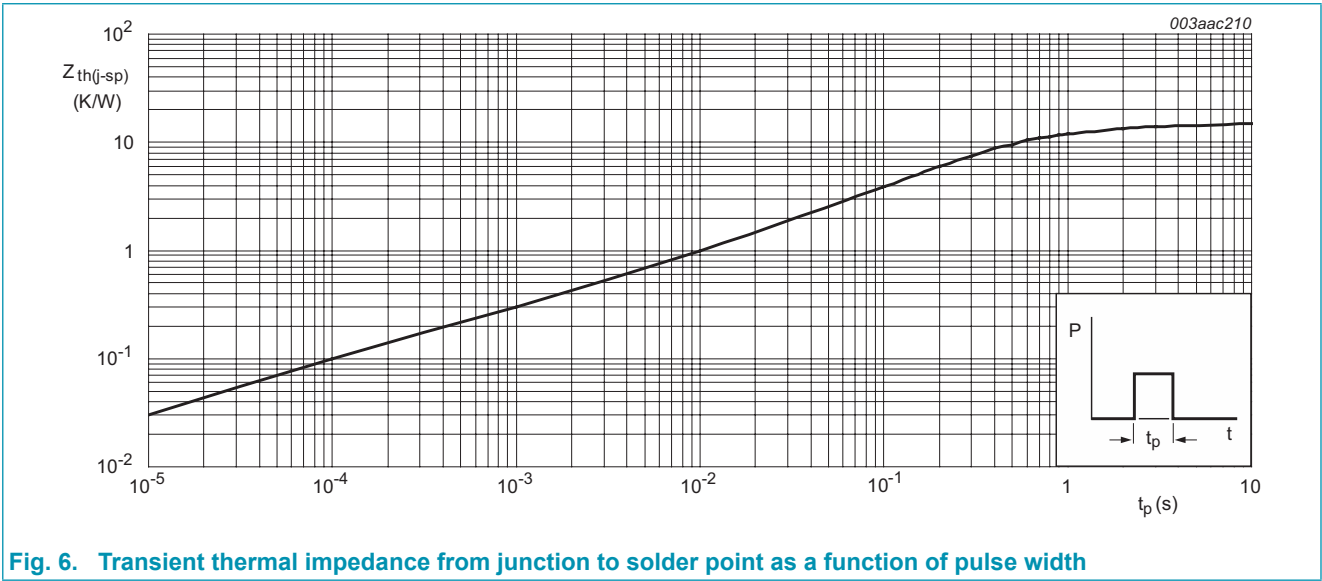
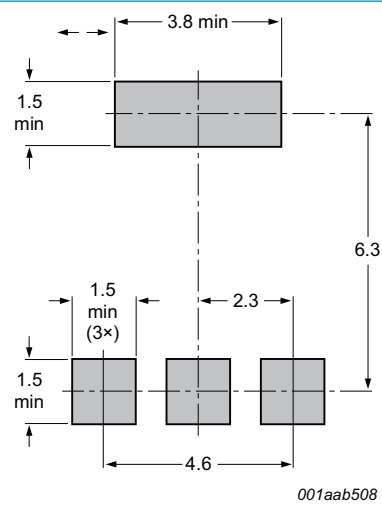
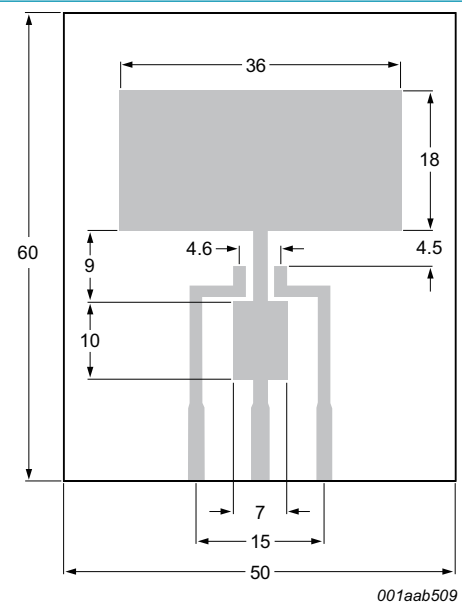


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width



All dimensions are in mm
Fig. 7. Minimum footprint SOT223

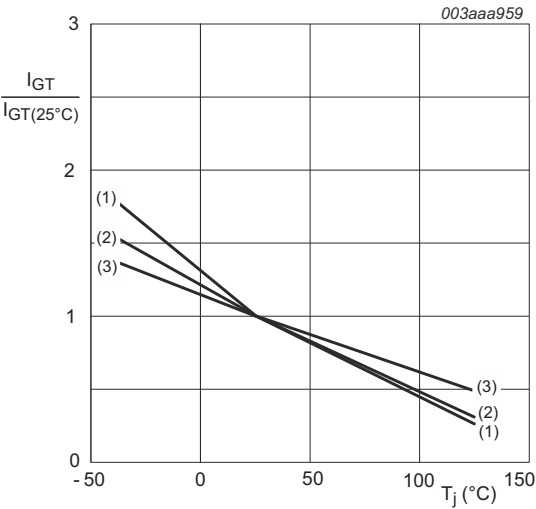


All dimensions are in mm
Printed circuit board:
FR4 epoxy glass (1.6 mm thick), copper laminate
(35 um thick)
Fig. 8. Printed circuit board pad area: SOT223

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		0.25	-	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		0.25	-	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		0.25	-	5	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	-	10	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	-	20	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	-	10	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 11		-	-	10	mA
V_T	on-state voltage	$I_T = 0.85\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 12		-	1.35	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 13		-	0.9	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 125\text{ }^\circ\text{C}$		0.2	0.3	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; $R_{GK} = 220\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform		200	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 0.8\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit		0.5	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

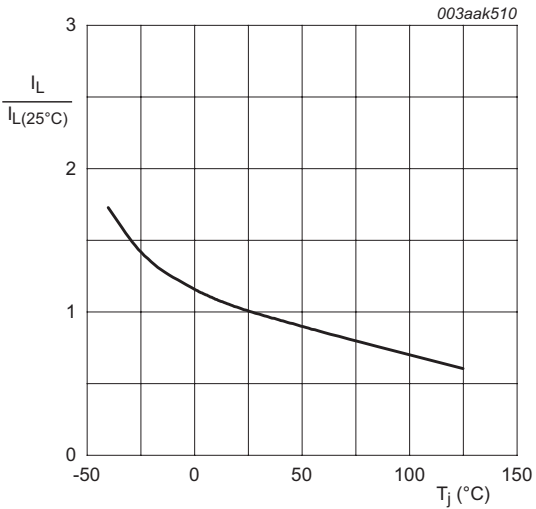


Fig. 10. Normalized latching current as a function of junction temperature

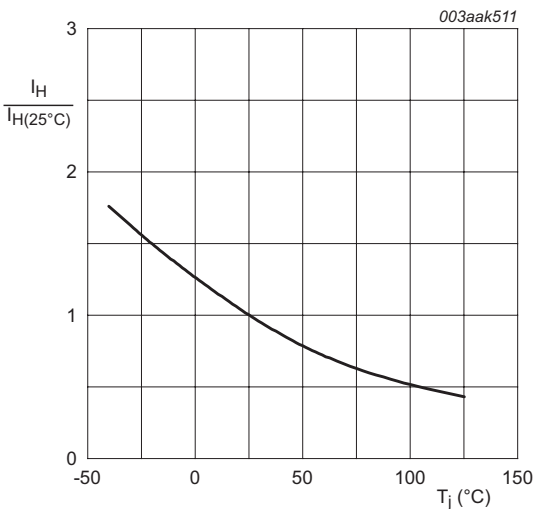
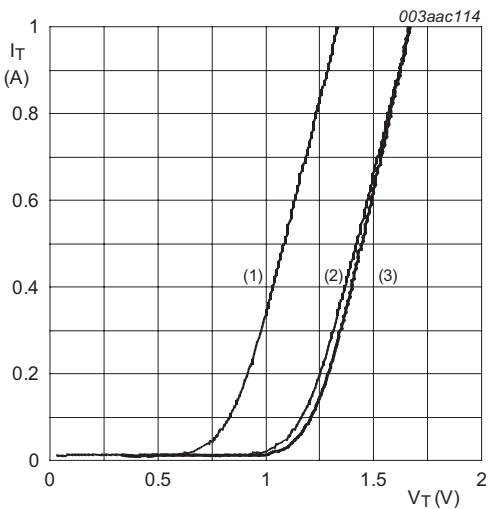


Fig. 11. Normalized holding current as a function of junction temperature



- $V_o = 0.835 \text{ V}$; $R_s = 0.50 \Omega$
- (1) $T_j = 125^{\circ}\text{C}$; typical values
 - (2) $T_j = 125^{\circ}\text{C}$; maximum values
 - (3) $T_j = 25^{\circ}\text{C}$; maximum values

Fig. 12. On-state current as a function of on-state voltage

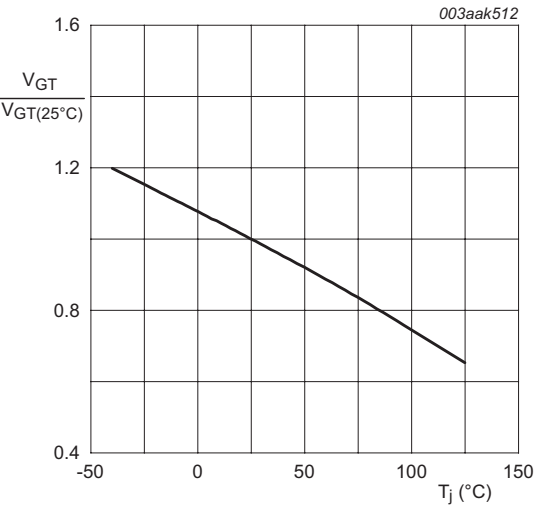
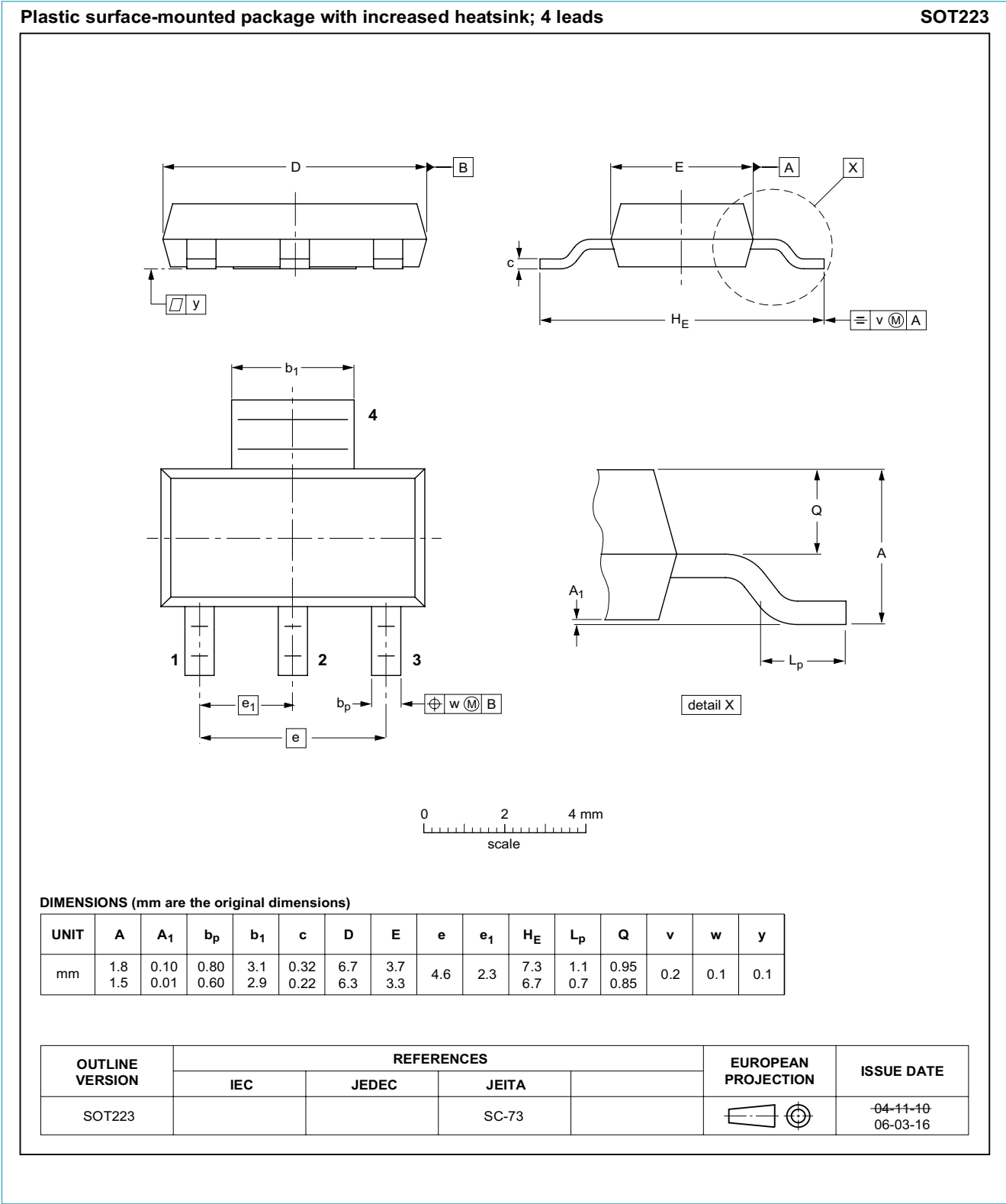


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Assembly factory: d & L



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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